[CLAIMS]

[Claim 1]

A Cr-Ti alloy sputtering target material, which is represented by a composition formula Cr_{100-X}-Ti_X, $40 \leq X \leq 60$ in terms of an atomic ratio, with the balance consisting of unavoidable impurities that comprise Mg, Al, Si, Mn, Ni, Cu and Sn in an amount of 1 ppm by mass or more and 50 ppm by mass or less in total.

[Claim 2]

The Cr-Ti alloy sputtering target material according to claim 1, wherein Mg≤1 ppm by mass, Al≤10 ppm by mass, Si≤10 ppm by mass, Mn≤1 ppm by mass, Ni≤10 ppm by mass, Cu≤1 ppm by mass, and Sn≤5 ppm by mass.

[Claim 3]

A method of preparing a Cr-Ti alloy sputtering target material, comprising:

mixing a Ti powder that comprises, as impurities, Mg, Al, Si, Mn, Ni, Cu and Sn in an amount of 1 ppm by mass or more and 50 ppm by mass or less in total, and a Cr powder that comprises, as impurities, Mg, Al, Si, Mn, Ni, Cu and Sn in an amount of 1 ppm by mass or more and 50 ppm by mass or less in total; and

sintering under pressure to obtain a Cr-Ti alloy sputtering target material, which is represented by a composition formula Cr_{100-X}-Ti_X, $40 \leq X \leq 60$ in terms of the atomic ratio, with the balance consisting of unavoidable impurities that comprises Mg, Al, Si, Mn, Ni, Cu and Sn in an amount of 1 ppm by mass or more and 50 ppm by mass or less in total.

[Claim 4]

The method according to claim 3, wherein, in the Ti powder, Mg≤1 ppm by mass, Al≤2 ppm by mass, Si≤10 ppm by mass, Mn≤2 ppm by mass, Ni≤10 ppm by mass,

Cu≤10 ppm by mass, and Sn≤2 ppm by mass.

[Claim 5]

The method according to claim 4, wherein, in the Cr powder, Mg≤1 ppm by mass, Al≤10 ppm by mass, Si≤10 ppm by mass, Mn≤1 ppm by mass, Ni≤10 ppm by mass, Cu≤1 ppm by mass, and Sn≤10 ppm by mass.